

H3/IPS
D. Brown
3-12-02

Sheet 1 of 2

FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. H-530-04		SERIAL NO.	
LIST OF DOCUMENTS CITED BY APPLICANT <i>(Use several sheets if necessary)</i>				APPLICANT T. ISHII et al		GROUP 2823	
				FILING DATE November 28, 2001			
U.S. PATENT DOCUMENTS							
* EXAMINER INITIAL	DOCUMENT	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)	
NB	AA	5,386,381	01/31/95	Takizawa et al	365	104	
NB	AB	5,214,296	05/00/93	Nakata et al	257	71	
NB	AC	5,258,625	11/02/93	Kamohara et al	257	14	
NB	AD	4,639,893	01/00/87	Eitan	365	185	
	AE	5,386,381	01/00/95	Takizawa et al	<i>cited above already</i>		
NB	AF	5,291,047	03/00/94	Iwasa	257	318	
NB	AG	5,625,217	12/00/92	Chau et al	257	412	
NB	AH	5,612,255	12/00/93	Chapple-Solol et al	437	203	
NB	AI	5,665,618	11/00/94	Meyer et al	438	172	
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
NB	AL 461764 A2	12/18/94	Europe	—	—	<input checked="" type="checkbox"/>	<input type="checkbox"/>
	AM					<input type="checkbox"/>	<input type="checkbox"/>
	AN					<input type="checkbox"/>	<input type="checkbox"/>
	AO					<input type="checkbox"/>	<input type="checkbox"/>
	AP					<input type="checkbox"/>	<input type="checkbox"/>
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, etc.)</i>							
NB	AR	Nikkei Electronics, No. 444, 1988, pp. 151-157.					
NB	AS	S. Tiwari et al, "A Low Power 77 K Nano-Memory with Single Electron Nano-Crystal Storage", 53rd ANNUAL DEVICE RESEARCH CONFERENCE DIGEST, 1995, pp. 50-51.					
NB	AT	T. Hashimoto et al, "An 8 nm-thick Polysilicon MOS Transistor and Its Thin Film Effects", 21st CONFERENCE ON SOLID-STATE DEVICES AND MATERIALS, 1989, pp. 97-100.					
EXAMINER <i>Neal Berezny</i>				DATE CONSIDERED <i>11-8-02</i>			

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
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	AM						<input type="checkbox"/>	<input type="checkbox"/>
	AN						<input type="checkbox"/>	<input type="checkbox"/>
	AO						<input type="checkbox"/>	<input type="checkbox"/>
	AP						<input type="checkbox"/>	<input type="checkbox"/>

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

NB	AR	K. Yano et al, "Room-Temperature Single-Electron Memory", IEEE TRANSACTIONS
		ON ELECTRON DEVICES, Vol. 41, No. 9, September 1994, pp. 1628-1638.
NB	AS	K. Yano et al, "A Room-Temperature Single-Electron Memory Device Using Fine-Grain Polycrystalline Silicon", INTERNATIONAL ELECTRON DEVICES MEETING,
		December 5-8, 1993, pp. 21.2.1 - 21.2.4.
	AT	

EXAMINER <i>Neal Bereszny</i>	DATE CONSIDERED <i>11-8-02</i>
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